## Diego Calvo Ruiz

## List of Publications by Year

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Articl

High-Speed Steep-Slope GalnAs Impact Ionization MOSFETs (I-MOS) With <i>SS</i>=1.25 mV/decâ€"Part II: Dynamic Switching and RF Performance. IEEE Transactions on Electron Devices, 2022, 69, 3549-3556.

High-Speed Steep-Slope GaInAs Impact Ionization MOSFETs (I-MOS) With SS = $1.25 \mathrm{mV} /$ decâ $€^{\prime \prime}$ Part I: Material 2 and Device Characterization, DC Performance, and Simulation. IEEE Transactions on Electron Devices, 2022, 69, 3542-3548.

Impact of Reduced Gateâ€toâ€Source Spacing on Indium Phosphide High Electron Mobility Transistor
Performance. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000191.

Low-Noise Microwave Performance of 30 nm GalnAs MOS-HEMTs: Comparison to Low-Noise HEMTs. IEEE
Electron Device Letters, 2020, 41, 1320-1323.

InAs Channel Inset Effects on the DC, RF, and Noise Properties of InP pHEMTs. IEEE Transactions on
Electron Devices, 2019, 66, 4685-4691.
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6 New GalnAs/InAs/InP Composite Channels for mm-Wave Low-Noise InP HEMTs. , 2019, , .
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7 Impact lonization Control in 50 nm Low-Noise High-Speed InP HEMTs with InAs Channel Insets. , 2019, , .

8 Effects of Electrochemical Etching on InP HEMT Fabrication. IEEE Transactions on Semiconductor Manufacturing, 2019, 32, 496-501.

Evaluation of energy barriers for topological transitions of Si self-interstitial clusters by classical molecular dynamics and the kinetic activation-relaxation technique. , 2017, , .

Pt Gate Sink-In Process Details Impact on InP HEMT DC and RF Performance. IEEE Transactions on Semiconductor Manufacturing, 2017, 30, 462-467.
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